## Hot-Swap Controller IC Makes Ajustable Circuit Breaker

Use of a hot-swap controller IC provides inrush-current-limiting and circuitbreaker functions for medium to high-voltage circuit protection.

Medium- and high-voltage systems that range from 9V to 72V often require one or more of the following circuit capabilities: hot-swap control, circuit-breaker fault protection, and inrush current limiting.

The circuit of Figure 1 provides inrush current limiting and a reliable circuit-breaker function for the load (C1 and R2), yet contains only a p-channel MOSFET, a hot-swap controller IC, and two optional resistors (R1 and R3). Adding a low-value resistor at the MOSFET drain provides an adjustable trip-point and improved accuracy over the operating temperature range (Figure 2).

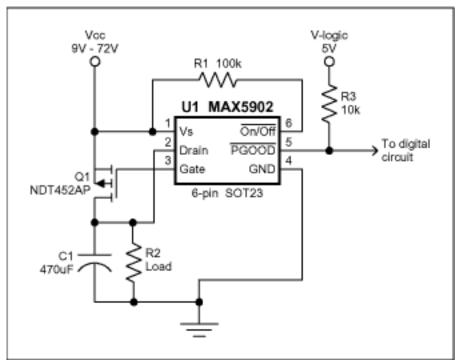


Figure 1. Standard circuit-breaker application.

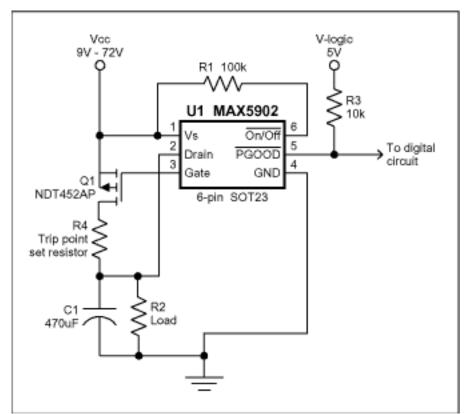


Figure 2. Adding a trip-point-adjust resistor (R4) to the circuit of Figure 1 improves its initial accuracy and accuracy over temperature.

For hot-swap applications, U1 limits the inrush current based on a typical gate-drive slew rate of 9V/mS. Inrush current is given by the equation I = CdV/dT = CSR, where C = Ioad capacitance and SR is the slew rate, set by U1 at 9V/mS (typical). For a Ioad capacitance of 100µF, the IC limits inrush current to approximately 0.9A.

U1's circuit-breaker function uses an internal comparator and the MOSFET on-resistance  $(R_{DS(ON)})$  to sense a fault condition.  $(R_{DS(ON)})$  for Q1 is typically 52m $\Omega$  and U1 has selectable circuit-breaker trip points (CB) of 300mV, 400mV, or 500mV. At the lowest trip point (300mV), the CB trip current at  $T_J = 25^{\circ}$  C is typically 5.77A.

The circuit breaker's voltage-trip value is determined from the equation  $V_{CB} > (R_{DS(ON)})I_{LOAD(MAX)}$ , or  $V_{CB}/I_{LOAD(MAX)} > (R_{DS(ON)})$ .

Suppose the desired limit is 2A. Using typical values,

 $300 \text{mV}/2\text{A} \approx 150 \text{m}\Omega > (\text{R}_{\text{DS(ON)}}).$ 

Instead of substituting another MOSFET with higher on-resistance, add a  $\approx 100 \text{m}\Omega$  resistor in series with Q1 (i.e., R4 in Figure 2). Besides allowing adjustable circuit-breaker levels, R4 provides better circuit-breaker accuracy and improved stability over temperature. For example, (R<sub>DS(ON)</sub>) for Q1 is  $\approx 52 \text{m}\Omega$  @ T<sub>J</sub> = 25° C and  $\approx 130 \text{m}\Omega$  @ T<sub>J</sub>=125C, a change of 150%. If you

add a  $100m\Omega$ ,  $100ppm/^{\circ}$  C resistor (which varies by  $0.001\Omega$  from 25° C to 125° C), the combined variance from 25° C ( $152m\Omega$ ) to  $125^{\circ}$  C ( $231m\Omega$ ) is only  $79m\Omega$ , which is 52%.

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## **More Information**

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